

Silicon NPN Power Transistors

2SD1344

DESCRIPTION

- With TO-3 package
- High voltage
- Built-in damper diode

APPLICATIONS

- For color TV horizontal deflection output applications

PINNING(see fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

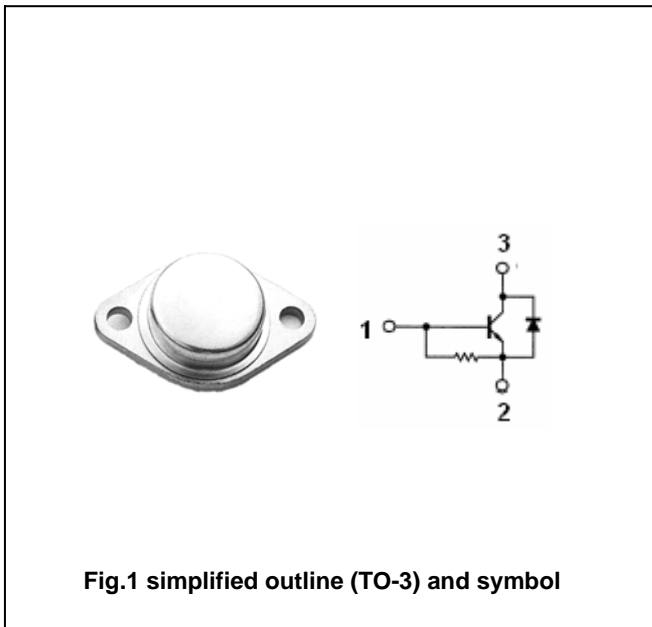


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	1500	V
V _{CEO}	Collector-emitter voltage	Open base	600	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		6	A
P _T	Total power dissipation	T _C =25°C	50	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-40~150	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CE0(SUS)}	Collector-emitter sustaining voltage	I _C =100m A; I _B =0	600			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =200m A; I _C =0	5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =4A; I _B =0.8 A			5.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =4A; I _B =0.8 A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =800V; I _E =0			10	μ A
h _{FE-1}	DC current gain	I _C =0.5A ; V _{CE} =5V	10			
h _{FE-2}	DC current gain	I _C =3A ; V _{CE} =5V	5			
V _F	Diode forward voltage	I _F =4A			2.0	V

PACKAGE OUTLINE

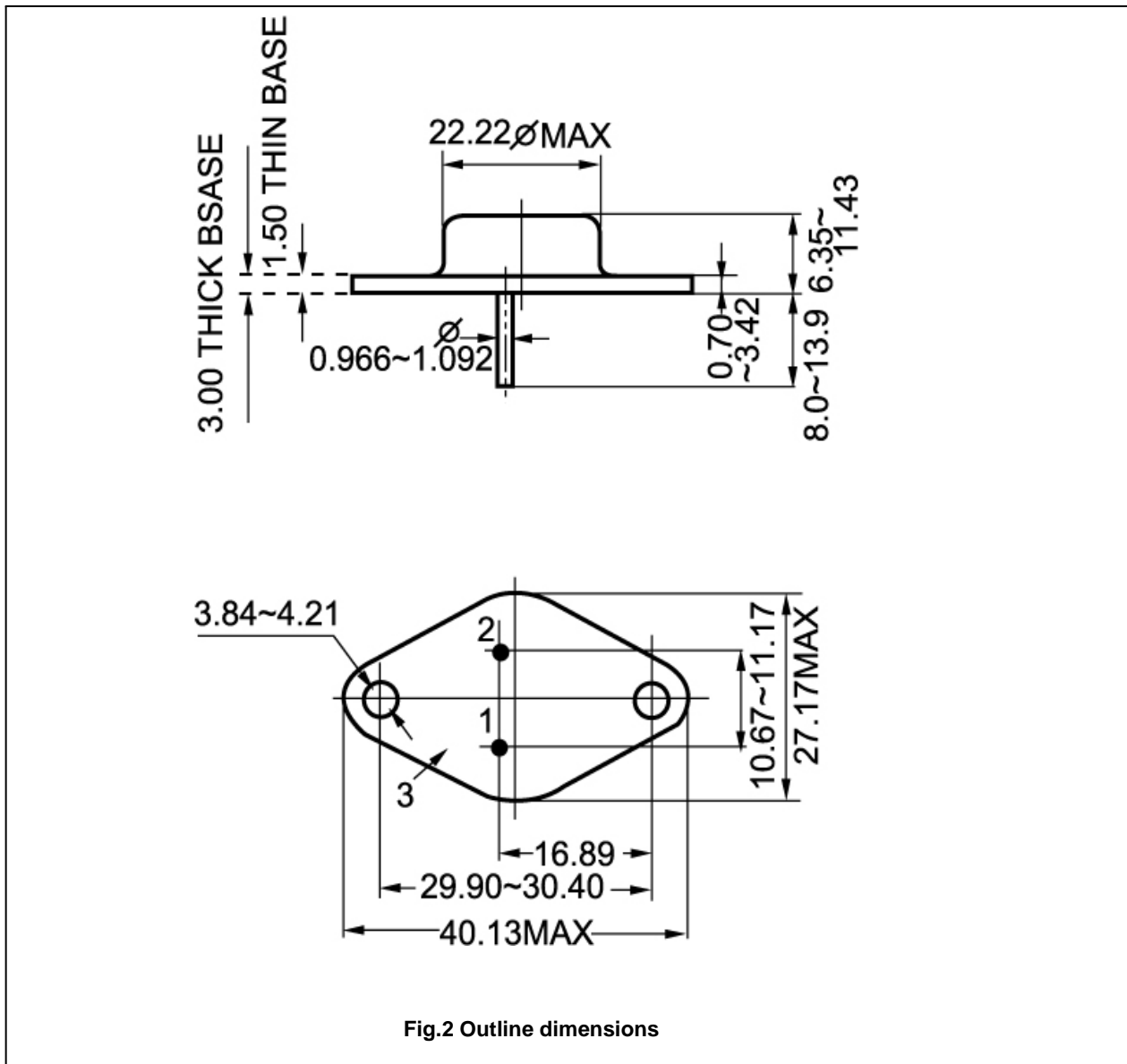


Fig.2 Outline dimensions